

EASTERN UNIVERSITY, SRI LANKA

SECOND EXAMINATION IN SCIENCE - 2001/2002

(APRIL 2002)

PH 202 ELECTRONICS I

Time: 01 hour.

Answer ALL Questions

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1. What do you mean by intrinsic semiconductor. Explain the formation of extrinsic

(a) *n - type*

(b) *p - type*

germanium semiconductor.

Discuss the mechanism of electrical conduction using energy band diagrams for above two cases.

A crystal is specified to be *n - type* silicon of  $15\Omega\text{cm}$  resistivity. Compute the electron and hole concentration. You may assume that the carrier concentration  $n_i = 1.5 \times 10^{10}\text{Cm}^{-3}$ , mobility of electron  $\mu_e = 1300\text{Cm}^2\text{V}^{-1}\text{s}^{-1}$  and the charge of electron  $e = 1.6 \times 10^{-19}\text{C}$ .

2. Explain briefly action of a transistor. Discuss the input and the output characteristics curves of a transistor.

A silicon transistor used in the following circuit may have any value of  $\beta$  between 36 and 90 at room temperature. The leakage current can be neglected at room temperature. Assume that  $R_c = 4\text{k}\Omega$ ,  $V_{cc} = 20\text{V}$ , the nominal bias point is to be at  $V_{CE} = 10\text{V}$ ,  $I_c = 2\text{mA}$  and  $I_c$  should be in the range  $1.75\text{mA}$  to  $2.25\text{mA}$  as  $\beta$  varies from 36 to 90. Find  $R_E$ ,  $R_1$  and  $R_2$ .

